



2SA608N/2SC536N

Low-Frequency General-Purpose Amplifier Applications

Applications

- Capable of being used in the low frequency to high frequency range.

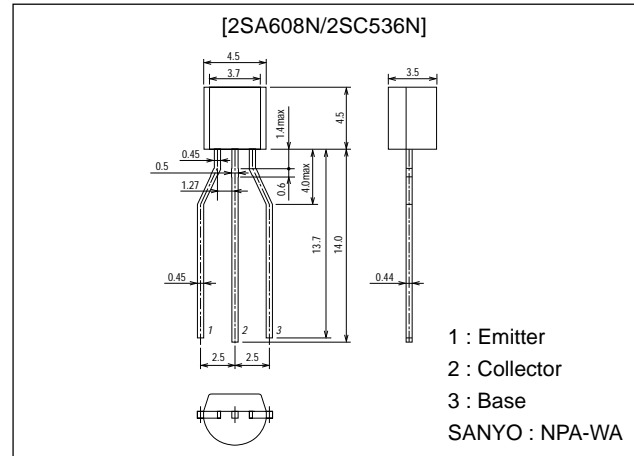
Features

- Large current capacity and wide ASO.

Package Dimensions

unit:mm

2164



() : 2SA608N

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-50)60	V
Collector-to-Emitter Voltage	V_{CE0}		(-50)	V
Emitter-to-Base Voltage	V_{EB0}		(-6)	V
Collector Current	I_C		(-150)	mA
Collector Current (Pulse)	I_{CP}		(-400)	mA
Collector Dissipation	P_C		500	mW
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)40V, I_E=0$			(-0.1)	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=(-)5V, I_C=0$			(-0.1)	μA
DC Current Gain	h_{FE1}	$V_{CE}=(-)6V, I_C=(-)1mA$	160*		560*	
	h_{FE2}	$V_{CE}=(-)6V, I_C=(-)0.1mA$	70			

Continued on next page.

* The 2SA608N/2SC536N are classified by 1mA h_{FE} as follow

Rank	F	G
h_{FE}	160 to 320	280 to 560

■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

■ SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

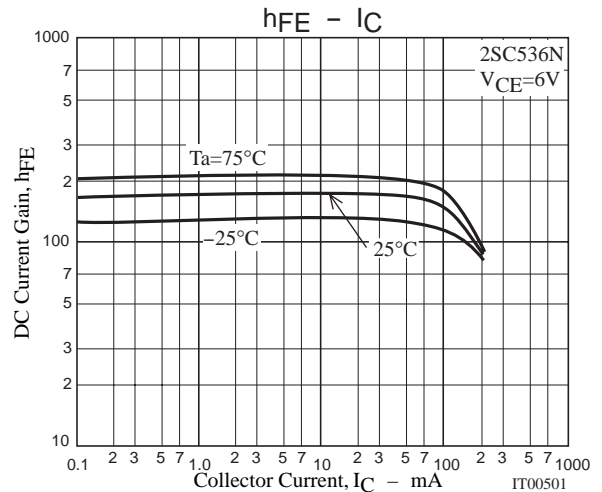
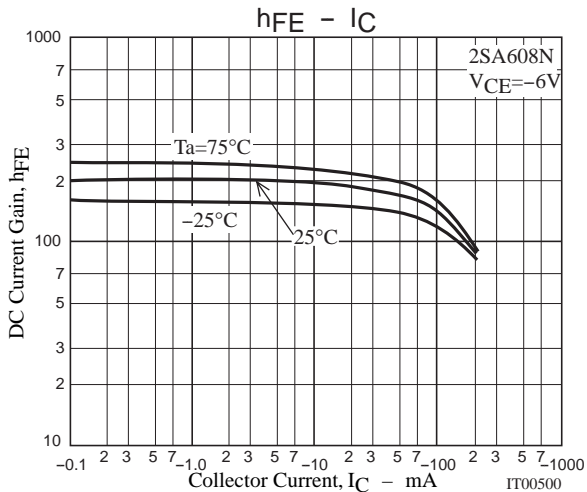
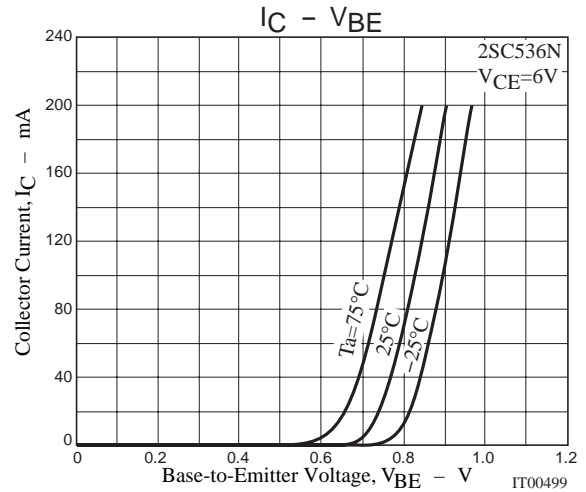
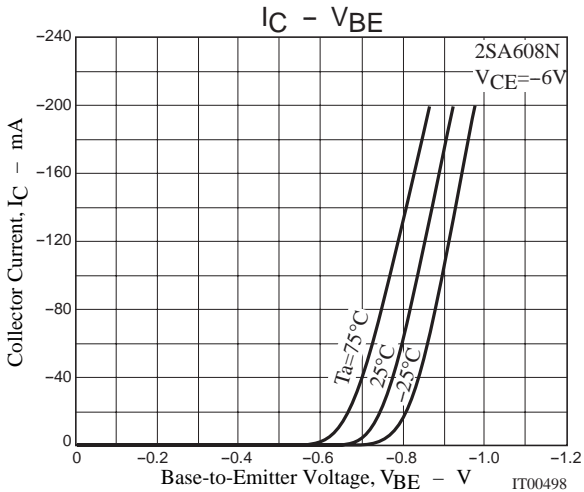
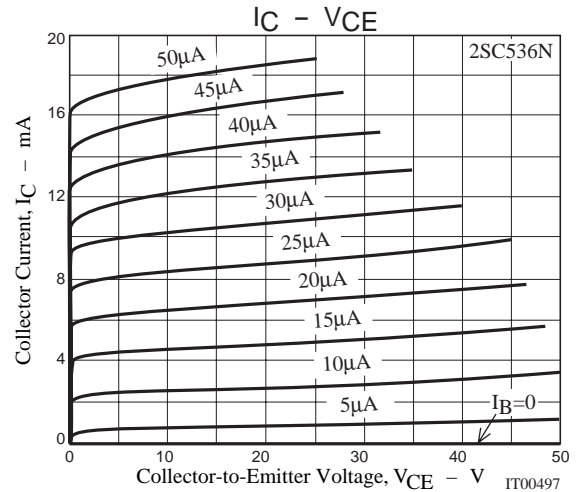
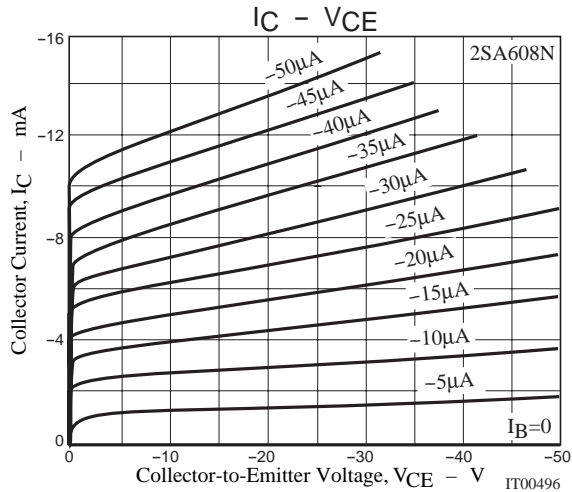
SANYO Electric Co., Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

2SA608N/2SC536N

Continued on preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)10mA$		200		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)6V, f=1MHz$		3.0		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$		(4.5)		pF
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$			(-1.0)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-60)			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-50)			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-6)			V



2SA608N/2SC536N

